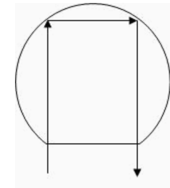
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.30 mm	
	2.0	Notch Direction	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Notch or Flat	Notch	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	1,000.00 +/- 15.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<35.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<35.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	<30um / Wafer edge polishgd or fine ground (No cracks)	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Frontsurface condition	Polished, surface roughness <1nm rms.	
	12.0	Flatness (SBIR)	<1um, 25mm X 25mm. No partials.	
	13.0	Front Surface Quality	No Particles >10um	
HandleSilicon	14.0	Handle Silicon Raw Material	Prime Silicon	
	15.0	Handle Growth Method	CZ	Wafer Vendor
	16.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	17.0	Handle Thickness	1,000.00 +/- 15.00 µm	ADE, 100%
	18.0	Handle Doping Type	P	Wafer Vendor
	19.0	Handle Dopant	Boron	Wafer Vendor
	20.0	Handle Resistivity	>1 Ohmcm	Wafer Vendor
	21.0	Backside Finish	Polished. Light handling scrtaches.	Wafer Vendor
	22.0	Surface Haze	none	Bright Light, 100% (note 2)

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

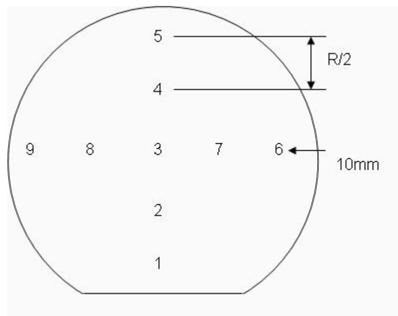
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information